

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>c</sub> = +25°C
60V	15mΩ @ V <sub>GS</sub> = 10V	32A
	24mΩ @ V <sub>GS</sub> = 4.5V	24A

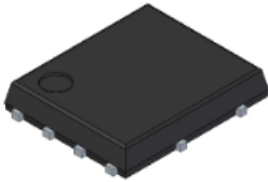
## Description and Applications

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and maintain superior switching performance, making it ideal for high efficiency power management applications.

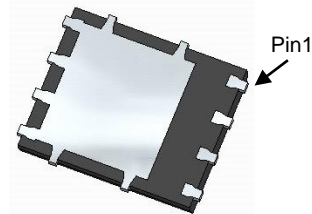
- Load Switch
- Adaptor Switch
- Notebook PC

Site1:

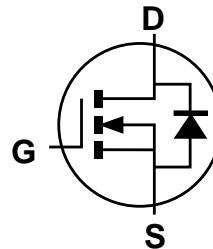
**PowerDI5060-8**



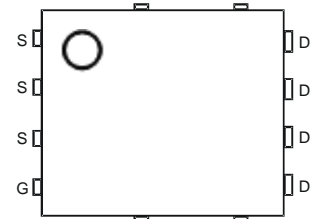
Top View



Bottom View



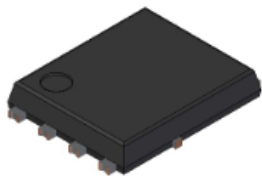
Internal Schematic



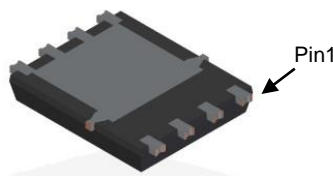
Top View  
Pin Configuration

Site2:

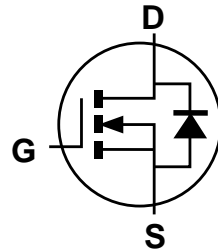
**PowerDI5060-8 (SWP) (Type UX)**



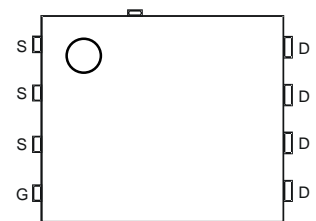
Top View



Bottom View



Internal Schematic



Top View  
Pin Configuration

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6016LPS-13	PowerDI5060-8	2,500/Tape & Reel
DMT6016LPS-13	PowerDI5060-8 (SWP) (Type UX)	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

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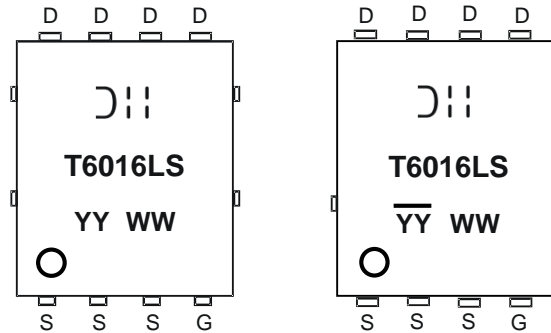
## Features

- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- Thermally Efficient Package - Cooler Running Applications
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile – Ideal for Thin Applications
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact_us) or your local Diodes representative.**  
<https://www.diodes.com/quality/product-definitions/>

## Mechanical Data

- Case: PowerDI5060-8
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (E3)
- Terminal Connections: See Diagram Below
- Weight: 0.097 grams (Approximate)

## Marking Information

**PowerDI5060-8/PowerDI5060-8 (SWP) (Type UX)**


= Manufacturer's Marking  
 T6016LS = Product Type Marking Code  
 YYWW or  $\overline{YY}WW$  = Date Code Marking  
 YY or  $\overline{YY}$  = Last Two Digits of Year (ex: 20 = 2020)  
 WW = Week Code (01 to 53)

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V <sub>DSS</sub>	60	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	T <sub>C</sub> = +25°C T <sub>C</sub> = +70°C	I <sub>D</sub>	32 25	A
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	10 8	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	60	A
Maximum Continuous Body Diode Forward Current (Note 6)		I <sub>S</sub>	2	A
Avalanche Current (Note 8) L = 0.1mH		I <sub>AS</sub>	15.3	A
Avalanche Energy (Note 8) L = 0.1mH		E <sub>AS</sub>	11.7	mJ

## Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P <sub>D</sub>	1.23	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	102	°C/W
	t < 10s		52	
Total Power Dissipation (Note 6)		P <sub>D</sub>	2.55	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	49	°C/W
	t < 10s		24	
Thermal Resistance, Junction to Case (Note 7)		R <sub>θJC</sub>	4.8	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
  - Thermal resistance from junction to soldering point (on the exposed drain pad).
  - I<sub>AS</sub> and E<sub>AS</sub> rating are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 9)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 9)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	—	2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	—	15	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A
		—	—	24		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 18A
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS (Note 10)</b>						
Input Capacitance	C <sub>iss</sub>	—	864	—	pF	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	282	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	27	—		
Gate Resistance	R <sub>G</sub>	—	1.3	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	8.4	—	nC	V <sub>DS</sub> = 30V, I <sub>D</sub> = 10A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	17	—		
Gate-Source Charge	Q <sub>gs</sub>	—	3.1	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	4.3	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	3.4	—	ns	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 30V, R <sub>G</sub> = 6Ω, I <sub>D</sub> = 10A
Turn-On Rise Time	t <sub>R</sub>	—	5.2	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	13	—		
Turn-Off Fall Time	t <sub>F</sub>	—	7	—		
Reverse Recovery Time	t <sub>RR</sub>	—	22	—	ns	I <sub>F</sub> = 10A, di/dt = 100A/μs
Reverse Recovery Charge	Q <sub>RR</sub>	—	11	—	nC	

Notes: 9. Short duration pulse test used to minimize self-heating effect.  
10. Guaranteed by design. Not subject to product testing.

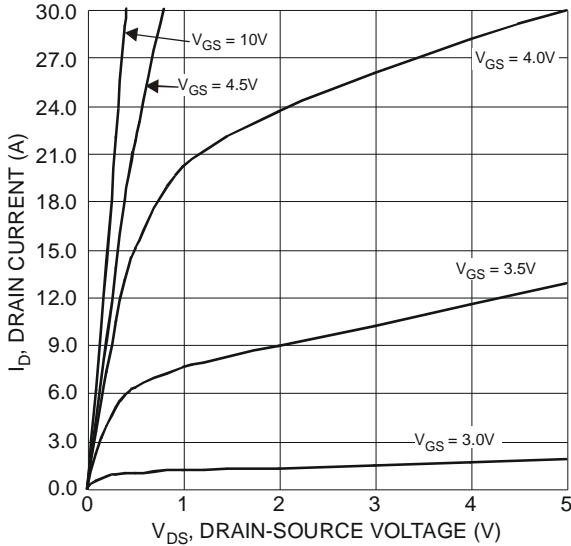


Figure 1 Typical Output Characteristics

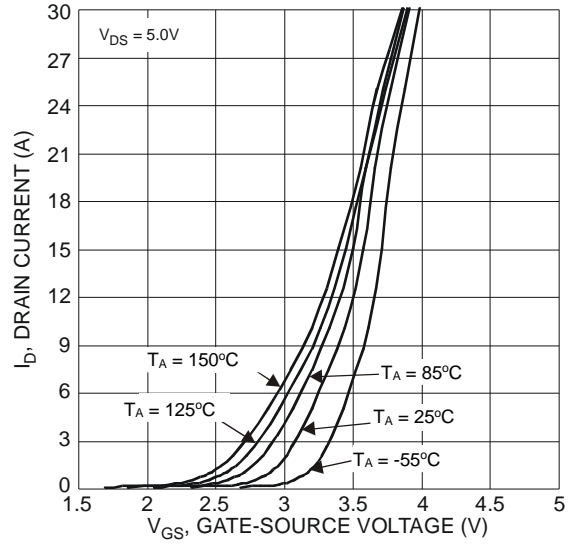


Figure 2 Typical Transfer Characteristics

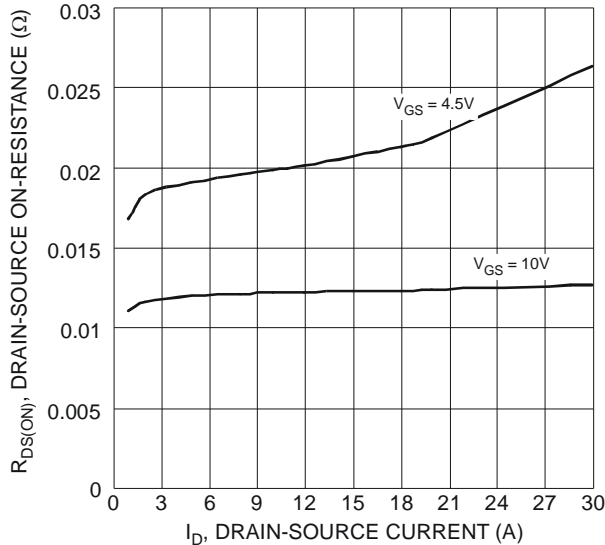


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

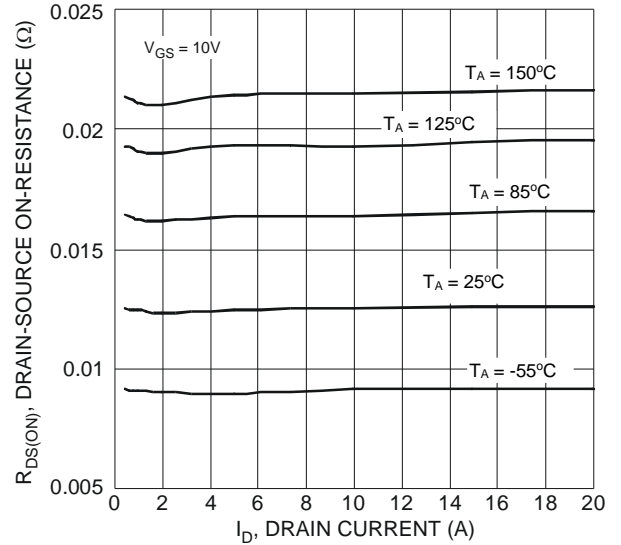


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

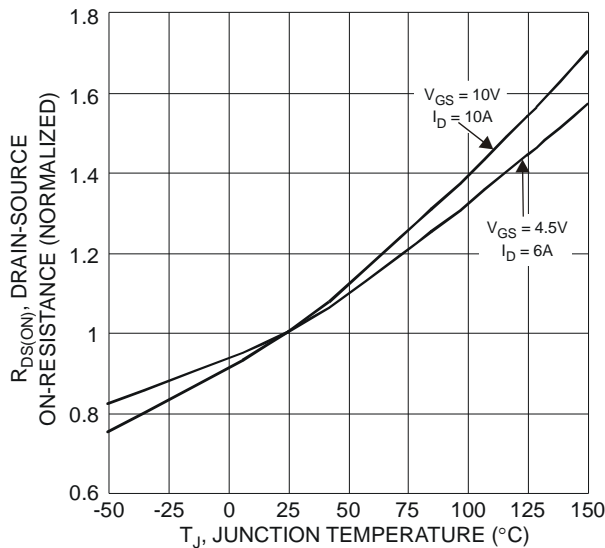


Figure 5 On-Resistance Variation with Temperature

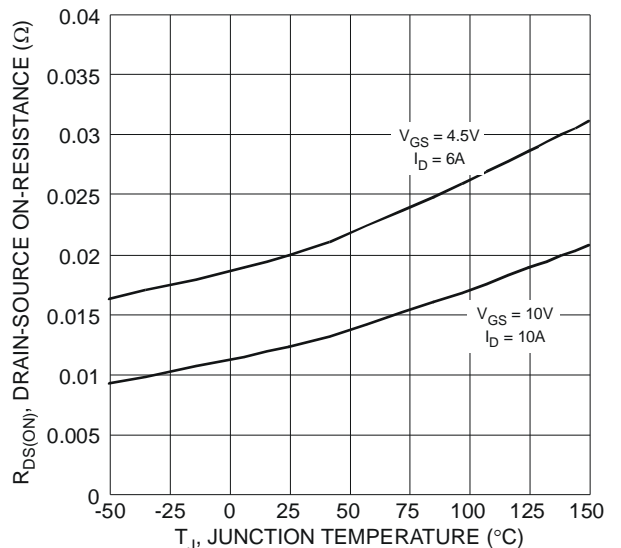


Figure 6 On-Resistance Variation with Temperature

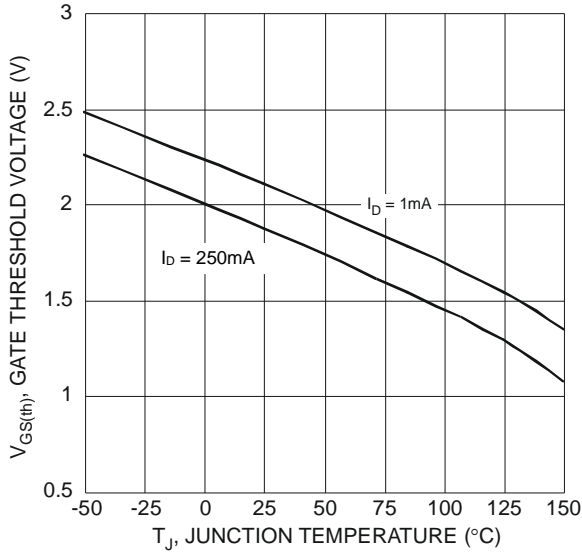


Figure 7 Gate Threshold Variation vs. Junction Temperature

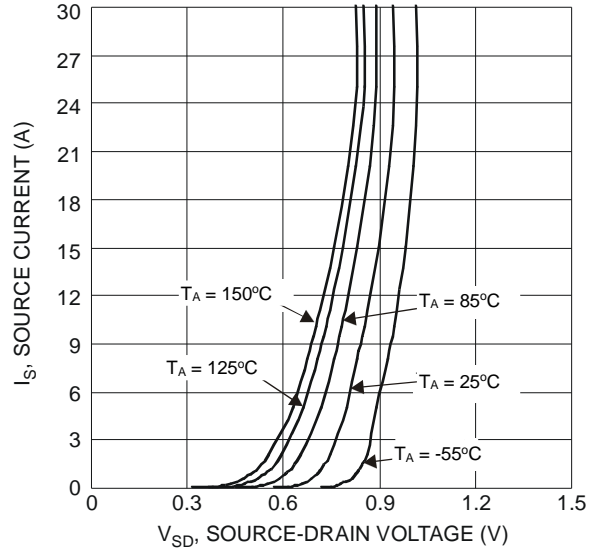


Figure 8 Diode Forward Voltage vs. Current

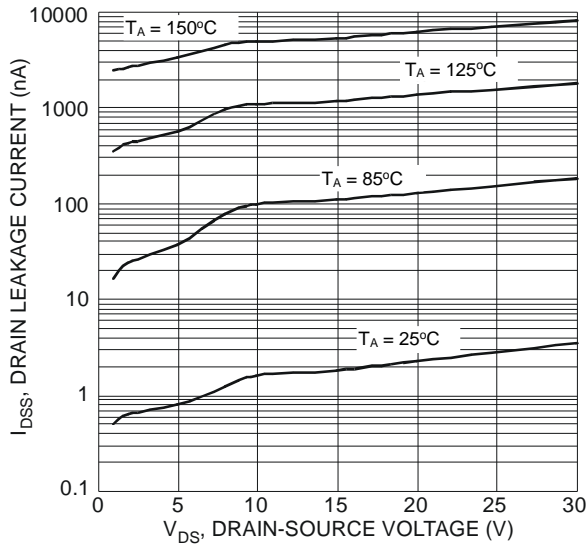


Figure 9 Typical Drain-Source Leakage Current vs. Voltage

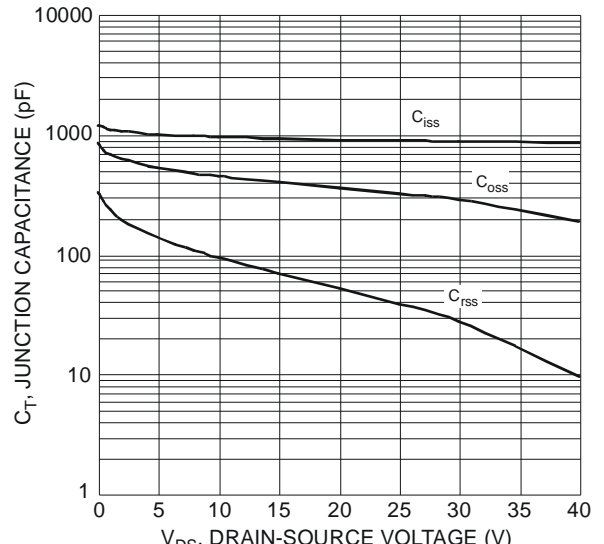


Figure 10 Typical Junction Capacitance

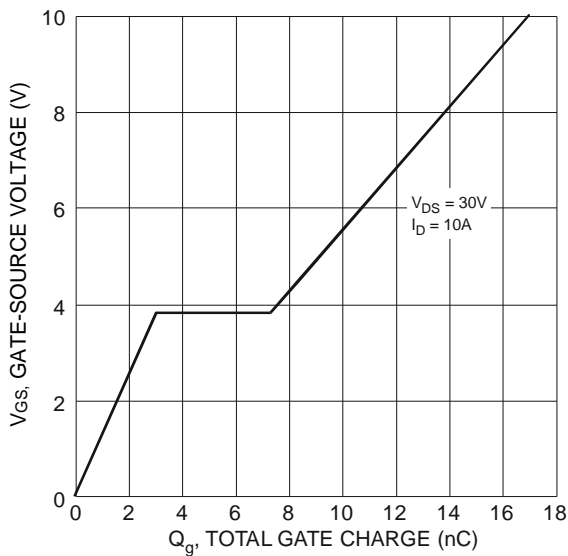


Figure 11 Gate Charge

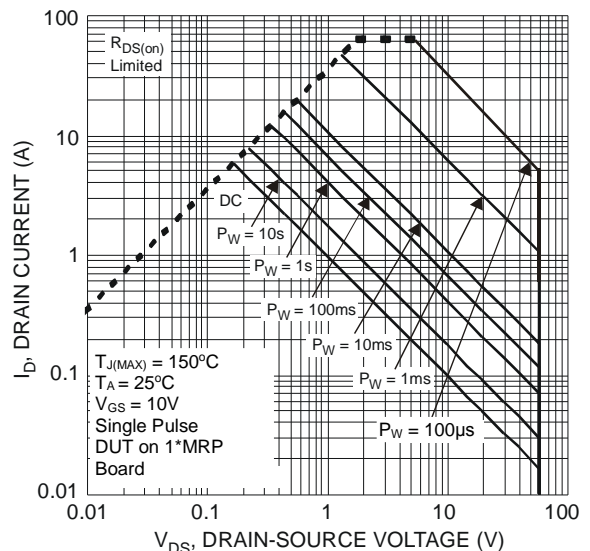


Figure 12 SOA, Safe Operation Area

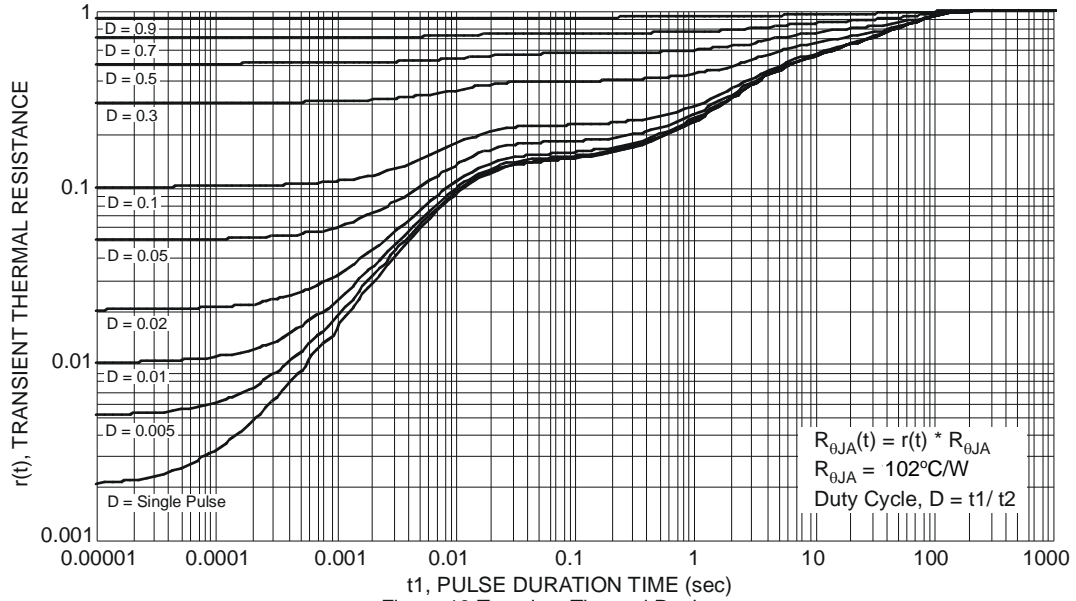


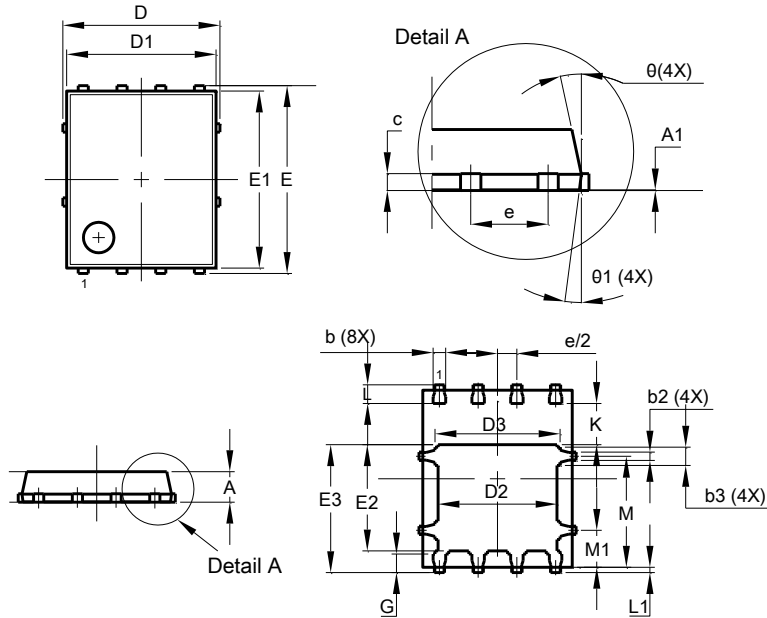
Figure 13 Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site1:

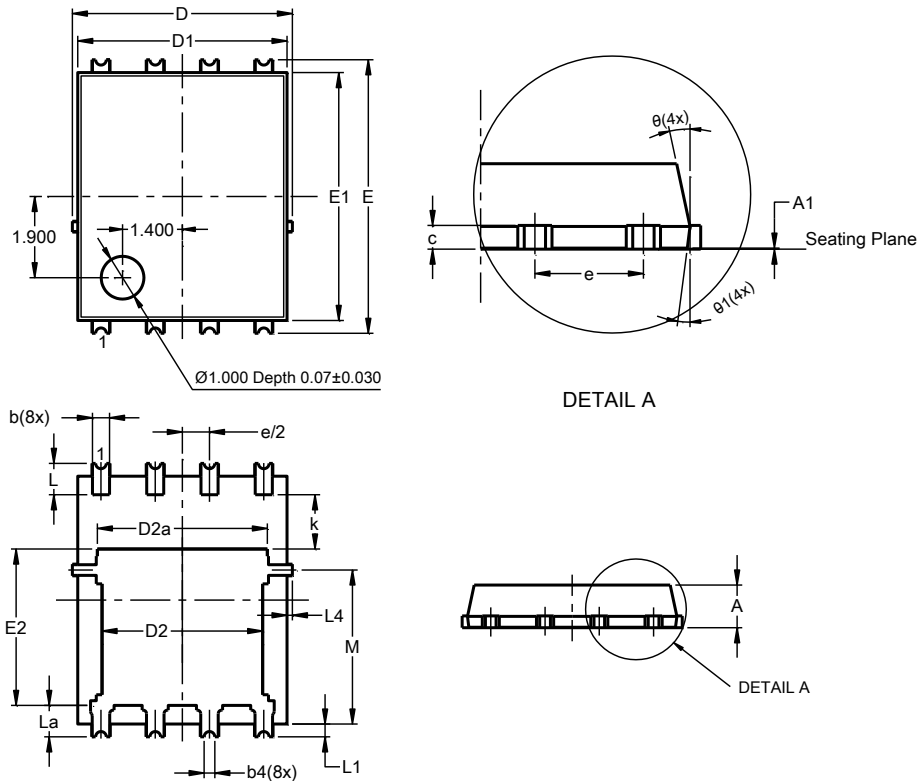
**PowerDI5060-8**



PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	--
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	--	--
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
theta	10°	12°	11°
theta1	6°	8°	7°
All Dimensions in mm			

Site2:

**PowerDI5060-8 (SWP) (Type UX)**



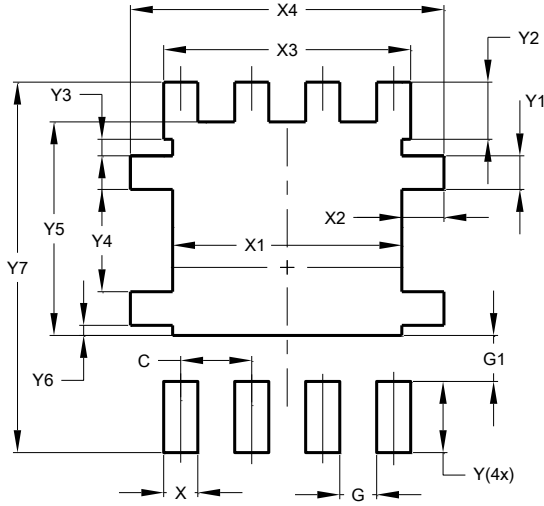
PowerDI5060-8 (SWP) (Type UX)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
theta	10°	12°	11°
theta1	6°	8°	7°
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site1:

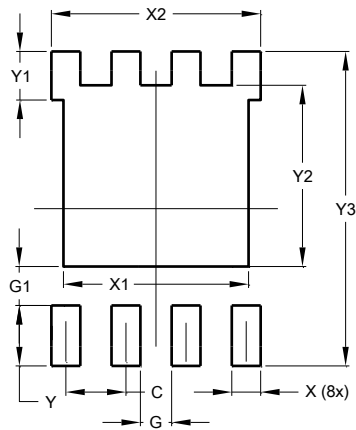
**PowerDI5060-8**



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

Site2:

**PowerDI5060-8 (SWP) (Type UX)**



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610



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